

# Mustapha Diani

## List of Publications by Year in descending order

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52  
papers

499  
citations

840776

11  
h-index

794594

19  
g-index

52  
all docs

52  
docs citations

52  
times ranked

314  
citing authors

#	ARTICLE	IF	CITATIONS
1	Search for carbon nitride CN <sub>x</sub> compounds with a high nitrogen content by electron cyclotron resonance plasma deposition. <i>Diamond and Related Materials</i> , 1994, 3, 264-269.	3.9	67
2	The Ge Stranski-Krastanov growth mode on Si(001) (2 Å <sup>-1</sup> ) tested by X-ray photoelectron and Auger electron diffraction. <i>Surface Science</i> , 1993, 291, 110-116.	1.9	32
3	A particular epitaxial Si <sub>1-x</sub> C <sub>y</sub> alloy growth mode on Si(001) evidenced by cross-sectional transmission electron microscopy. <i>Journal of Crystal Growth</i> , 1995, 157, 420-425.	1.5	24
4	X-ray photoelectron diffraction observation of $\beta$ -SiC(001) obtained by electron cyclotron resonance plasma assisted growth on Si(001). <i>Applied Surface Science</i> , 1993, 68, 575-582.	6.1	23
5	A First-Principles Investigation on Electronic Structure, Optical and Thermoelectric Properties of Janus In <sub>2</sub> SeTe Monolayer. <i>Journal of Superconductivity and Novel Magnetism</i> , 2021, 34, 3279-3290.	1.8	23
6	Strong element dependence of C 1s and Si 2p X-ray photoelectron diffraction profiles for identical C and Si local geometries in $\beta$ -SiC. <i>Surface Science</i> , 1995, 339, 363-371.	1.9	20
7	Oxygen vacancies and defects tailored microstructural, optical and electrochemical properties of Gd doped CeO <sub>2</sub> nanocrystalline thin films. <i>Materials Science in Semiconductor Processing</i> , 2022, 145, 106631.	4.0	20
8	Selective thermal nitridation as opposed to non-selective plasma nitridation of Si <sub>1-x</sub> Ge related materials examined by in situ photoemission techniques. <i>Journal of Non-Crystalline Solids</i> , 1995, 187, 319-323.	3.1	15
9	Electronic structure, optical and thermoelectric properties of Ge <sub>2</sub> SeS monolayer via first-principles study. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2022, 136, 115022.	2.7	15
10	Crystal growth of $\beta$ -SiC polytype on $\beta$ -SiC(0001) substrate. <i>Journal of Crystal Growth</i> , 2002, 235, 95-102.	1.5	13
11	An experimental characterization of Si(111) surfaces by Si 2p X-ray photoelectron diffraction. <i>Solid State Communications</i> , 1992, 83, 823-827.	1.9	12
12	Observation of Si out-diffusion related defects in SiC growth on Si(001). <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1995, 29, 110-113.	3.5	11
13	Synthesis of epitaxial Si <sub>1-x</sub> C <sub>y</sub> alloys on Si(001) with high level of non-usual substitutional carbon incorporation. <i>Journal of Crystal Growth</i> , 1995, 157, 431-435.	1.5	10
14	Tailoring the germanene-substrate interactions by means of hydrogenation. <i>Physical Chemistry Chemical Physics</i> , 2016, 18, 15667-15672.	2.8	10
15	Performance evaluation and analysis of polycrystalline photovoltaic plant located in Northern Morocco. <i>International Journal of Ambient Energy</i> , 2022, 43, 1262-1268.	2.5	10
16	First-principles study on electronic and thermoelectric properties of Janus monolayers AsXC <sub>3</sub> (X: Sb, Bi). <i>Journal of Superconductivity and Novel Magnetism</i> , 2021, 34, 1071-1077.	2.1	10
17	First-principles calculations to investigate structural, electronic and optical properties of Janus AsMC <sub>3</sub> (M: Sb, Bi) monolayers for optoelectronic applications. <i>Solid State Communications</i> , 2022, 343, 114667.	1.9	10
18	Ge quantum dots on a large band gap semiconductor: the first growth stages on $\beta$ -SiC(0001). <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 23, 428-434.	2.7	9



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37	In-situ surface technique analyses and ex-situ characterization of Si <sub>1-x</sub> Ge <sub>x</sub> epilayers grown on Si(001)-2 Å <sup>-1</sup> by molecular beam epitaxy. <i>Journal De Physique III</i> , 1994, 4, 733-740.	0.3	5
38	Tunable properties of the stable SiSeS Janus monolayer under biaxial strain: First-principles prediction. <i>Optik</i> , 2022, 261, 169123.	2.9	5
39	Si and Ge nanostructures epitaxy on a crystalline insulating LaAlO <sub>3</sub> (001) substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 657-662.	1.8	4
40	Experimental molecular adsorption: electronic buffer effect of germanene on Al(111). <i>2D Materials</i> , 2019, 6, 035016.	4.4	4
41	Biaxial strain engineering of the electronic and optical properties of Ge <sub>2</sub> SeS monolayer: Promising for optoelectronic applications. <i>Computational Condensed Matter</i> , 2022, 32, e00717.	2.1	4
42	Electron cyclotron resonance plasma ion beam effects on the formation of SiC on Si(001) characterized by in-situ photoemission. <i>Thin Solid Films</i> , 1994, 241, 305-309.	1.8	3
43	Ge epitaxial island growth on a graphitized C-rich 4H-SiC(0001) surface. <i>Journal of Crystal Growth</i> , 2005, 275, e2275-e2280.	1.5	3
44	Investigation of aluminum phthalocyanine chloride as acceptor material in planar organic solar cells: comparative study with fullerene. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 27710.	2.2	3
45	Strain enhanced electronic and optical properties in Janus monolayers AsMC <sub>3</sub> (M: Sb, Bi). <i>Physica B: Condensed Matter</i> , 2022, 642, 414143.	2.7	3
46	Growth of Fe nanocrystals on LaAlO <sub>3</sub> (001) and epitaxial relationship determination by RHEED and XPS. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1393-1396.	0.8	2
47	Performance evaluation and experimental validation of different empirical models for predicting photovoltaic output power. <i>International Journal of Ambient Energy</i> , 2022, 43, 7437-7453.	2.5	2
48	First-principles investigations of structural, electronic and thermoelectric properties of $\beta$ -Sb/Ge <sub>2</sub> van der Waals heterostructures. <i>Journal of Computational Electronics</i> , 2022, 21, 582-589.	2.5	2
49	Reply to the comment on "Search for carbon nitride CN <sub>x</sub> compounds with a high nitrogen content by electron cyclotron resonance plasma deposition", <i>Diamond relat. mater.</i> , 3 (1994) 264-269. <i>Diamond and Related Materials</i> , 1994, 3, 1279.	3.9	1
50	Chemical and structural transformations of silicon submitted to H <sub>2</sub> or H <sub>2</sub> /CH <sub>4</sub> microwave plasmas. <i>Diamond and Related Materials</i> , 2008, 17, 428-434.	3.9	1
51	Epitaxial growth of Fe islands on LaAlO <sub>3</sub> (001) substrates. <i>Journal of Crystal Growth</i> , 2014, 391, 121-129.	1.5	0
52	Synthesis, Structural and Optical Characteristics of Vanadium Doped Cerium Dioxide Layers. <i>SSRN Electronic Journal</i> , 0, , .	0.4	0